

## Silicon PNP Power Transistors

2SA1789

## DESCRIPTION

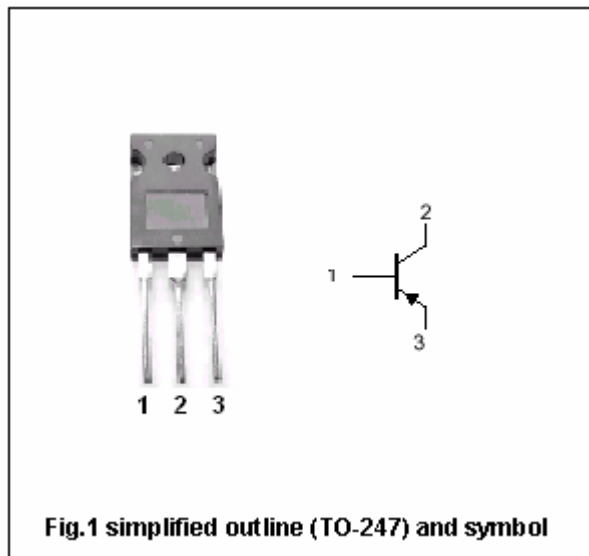
- With TO-247 package
- Complement to type 2SC4653
- Low collector saturation voltage

## APPLICATIONS

- For audio output applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-60	V
$V_{CEO}$	Collector-emitter voltage	Open base	-60	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-12	A
$P_C$	Collector power dissipation	$T_c=25^\circ\text{C}$	80	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

 $T_j=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25\text{mA}; I_B=0$	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1\text{mA}; I_E=0$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1\text{mA}; I_C=0$	-5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=-6\text{A}; I_B=-0.6\text{A}$			-0.5	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=-6\text{A}; I_B=-0.6\text{A}$			-2.0	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=-60\text{V}; I_E=0$			-10	$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=-5\text{V}; I_C=0$			-10	$\mu\text{A}$
$h_{FE}$	DC current gain	$I_C=-2\text{A}; V_{CE}=-2\text{V}$	60		320	

◆  $h_{FE}$  classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

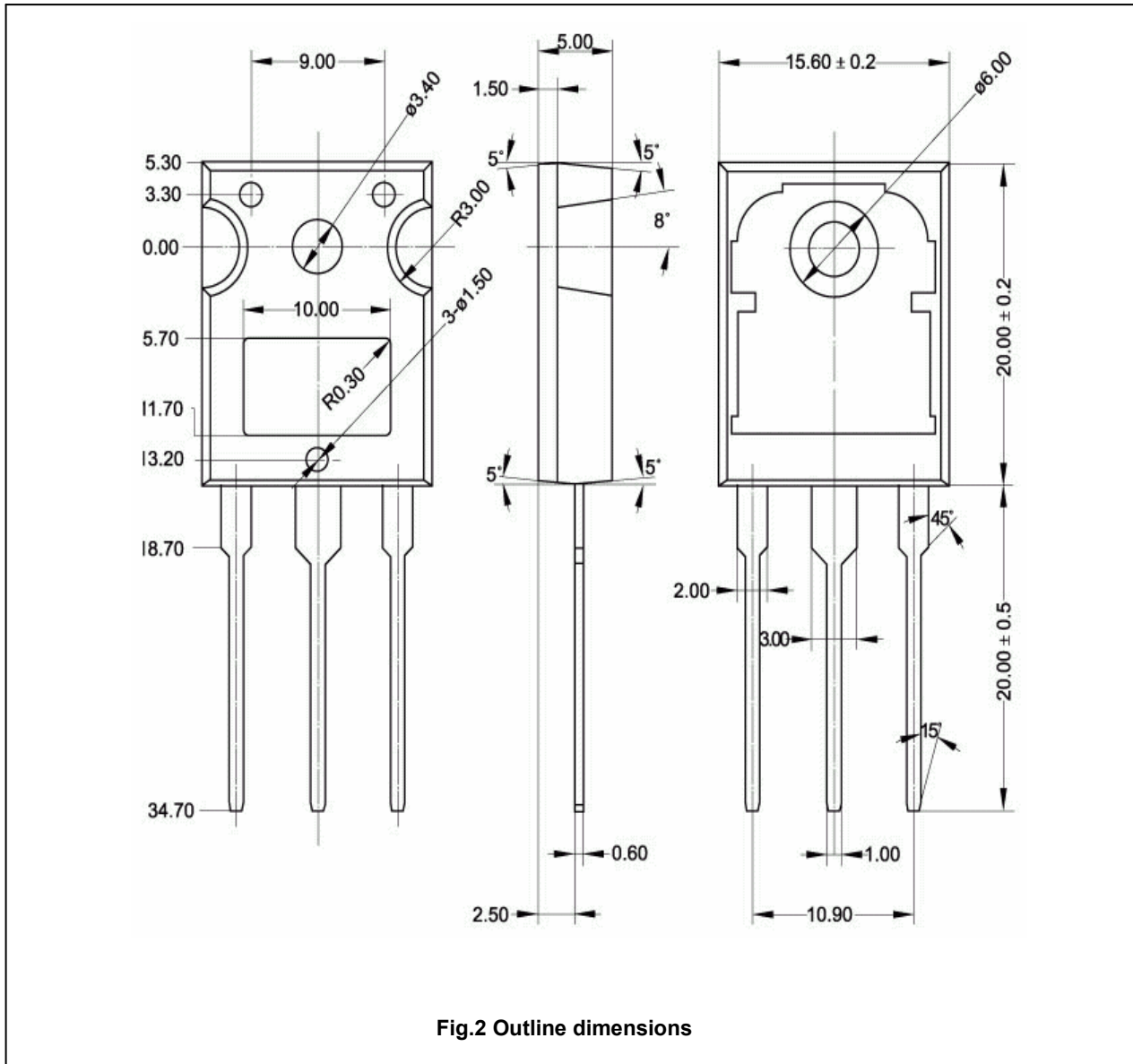


Fig.2 Outline dimensions